Agilent HMMC–5023
23 GHz LNA (21.2–26.5 GHz)

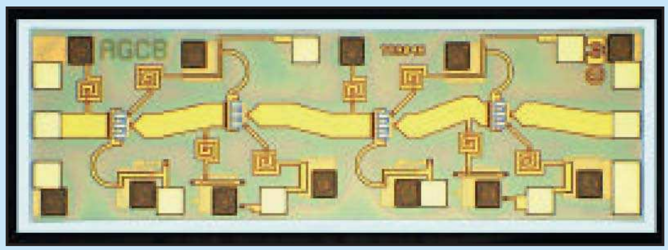
1GG6-8001
Data Sheet

Features

- Frequency range:
  21.2-23.6 GHz and
  24.5-26.5 GHz specified
  21-30 GHz performance
- Low-noise temperature:
  226 k (2.5 dB N.F.) typical
- High gain: 24 dB typical
- 50 Ω input/output matching
- Single supply bias with
  optional bias adjust:
  5 volts (@ 24 mA typical)

Description

The HMMC-5023 MMIC is a high-gain low-noise amplifier (LNA) that operates from 21 GHz to over 30 GHz. By eliminating the complex tuning and assembly processes typically required by hybrid (discrete–FET) amplifiers, the HMMC-5023 is a cost-effective alternative in both 21.2-23.6 GHz and 24.5-26.5 GHz communications receivers. The device has good input and output match to 50 ohms and is unconditionally stable to more than 40 GHz. The backside of the chip is both RF and DC ground. This helps simplify the assembly process and reduces assembly related performance variations and costs. It is fabricated using PHEMT integrated circuit structure that provides exceptional noise and gain performance.



Chip Size:	1880 × 600 µm (74 × 23.6 mils)
Chip Size Tolerance:	±10 µm (±0.4 mils)
Chip Thickness:	127 ±15 µm (5.0 ±0.6 mils)
Pad Dimensions:	80 × 80 µm (3.1 × 3.1 mils), or larger

Absolute Maximum Ratings[1]

Symbol	Parameters/Conditions	Min.	Max.	Units
V_{D1}, V_{D2}	Drain Supply Voltage	3	8	volts
V_{G1}, V_{G2}	Gate Supply Voltage	0.4	2	volts
I_{D1}	Drain Supply Current		35	mA
I_{D2}	Drain Supply Current		35	mA
P_{in}	RF Input Power[2]		15	dBm
T_{ch}	Channel Temperature[3]		150	°C
T_A	Backside Ambient Temperature	-55	+140	°C
T_{st}	Storage Temperature	-65	+165	°C
T_{max}	Max. Assembly Temperature		300	°C

[1] Absolute maximum ratings for continuous operation unless otherwise noted.
[2] Operating at this power level for extended (continuous) periods is not recommended.
[3] Refer to *DC Specifications/Physical Properties* table for derating information.

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DC Specifications/Physical Properties[1]

Symbol	Parameters/Conditions	Min.	Typ.	Max.	Units
V_{D1}, V_{D2}	Recommended Drain Supply Voltage	3	5	7	Volts
V_{G1}, V_{G2}	Gate Supply Voltage [$V_{D1} \leq V_{D1(max)}$, $V_{D2} \leq V_{D2(max)}$]	0.4	0.8[2]	2	Volts
I_{D1}, I_{D2}	Input and Output Stage Drain Supply Current ($V_{G1} = V_{G2}$ = Open, $V_{D1} = V_{D2}$ = 5 Volts)		12	35	mA
$I_{D1} + I_{D2}$	Total Drain Supply Current ($V_{G1} = V_{G2}$ = Open, $V_{D1} = V_{D2}$ = 5 Volts)	13	24	30	mA
$\theta_{ch\text{-}bs}$	Thermal Resistance[3] (Channel-to-Backside at T_{ch} = 150°C)		75		°C/Watt
T_{ch}	Channel Temperature[4] (T_A = 140 °C, MTTF = 10^6 hrs, $V_{G1} = V_{G2}$ = Open, $V_{D1} = V_{D2}$ = 5 Volts)		150		°C

1 Backside ambient operating temperature T_A = 25°C unless otherwise noted.
2 Open circuit voltage at V_{G1} and V_{G2} when V_{D1} and V_{D2} are 5 volts.
3 Thermal resistance (in °C/Watt) at a channel temperature T(°C) can be estimated using the equation: $\theta(T) = 75 \times [T(°C) + 273] / [150°C + 273]$.
4 Derate MTTF by a factor of two for every 8°C above T_{ch}.

RF Specifications

(T_{op} = 25°C, $V_{D1} = V_{D2}$ = 5 V, $V_{G1} = V_{G2}$ = Open, Z_0 = 50 Ω, unless otherwise noted)

Symbol	Parameters/Conditions		21.2-23.6 GHz			24.5-26.5 GHz			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
BW	Operating Bandwidth		21.2		23.6	24.5		26.5	GHz
Gain	Small Signal Gain		21	24	28	17	21	25	dB
Δ Gain	Small Signal Gain Flatness			±1			±1.5		dB
$(RL_{in})_{MIN}$	Minimum Input Return Loss		10	12		12	20		dB
$(RL_{out})_{MIN}$	Minimum Output Return Loss		8	10		8	10		dB
Isolation	Reverse Isolation		40	50		40	48		dB
$P_{-1\,dB}$	Output Power @ 1 dB Gain Compression			10			10		dBm
	Output Power @ 1 dB Gain Compression (V_D = 5 V, V_{G1}= Open, V_{D2} = 7 V, V_{G2} set for I_{D2} = 35 mA)			14			14		dBm
P_{SAT}	Saturated Output Power (@ 3 dB Gain Compression)			12			12		dBm
2nd Harm.	Second Harmonic Power Level [$f = 2f_0$, $P_{out}(f_0) = P_{-1\,dB}$, 21.2 GHz ≤ f_0 ≤ 23.6 GHz]			-30			-30		dBc
NF	Noise Figure	22 GHz		2.5	3.0				dB
		25 GHz					2.8	3.3	dB

Applications

The HMMC-5023 low noise amplifier (LNA) is designed for use in digital radio communication systems that operate within
the 21.2 to 23.6 GHz and 24.5 to 26.5 GHz frequency bands. High gain and low noise temperture make it ideally suited as a
front-end gain stage. The MMIC solution is a cost effective alternative to hybrid assemblies.

Biasing and Operation

The HMMC-5023 has four cascaded gain stages as shown Figure 1. The first two gain stages at the input are biased with the V_{D1} drain supply. Similarly the two output stages
are biased with the V_{D2} supply. Standard LNA operation is
with a single positive DC drain supply voltage ($V_{D1} = V_{D2} = 5$ V)
using the assembly diagram shown in Figure 8(a).

If desired, the output stage DC supply voltage (V_{D2}) can be increased to improve output power capability while maintaining optimum low noise bias conditions for the input section. The output power may also be adjusted by applying a positive voltage at V_{G2} to alter the operating bias point for both output FETs. Increasing the voltage applied to V_{G2} (more positively) results in a more negative gate-to-source voltage and, therefore, lower drain current. Figures 8(b) and 8(c) illustrate how the device can be assembled for both independent drain supply operation and for output-stage gate bias control.

No ground wires are required since ground connections are made with plated through-holes
to the backside of the device.

Assembly Techniques

It is recommended that the RF input and RF output connections be made using either 500 line/inch (or equivalent) gold wire mesh, or dual 0.7 mil diameter gold wire. The RF wires should be kept as short as possible to minimize inductance. The bias supply wire can be a 0.7 mil diameter gold wire attached to either of the V_{DD} bonding pads.

GaAs MMICs are ESD sensitive. ESD preventive measures must be employed in all aspects of storage, handling, and assembly.

MMIC ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful GaAs MMIC performance and reliability.

Agilent application note 54, “GaAs MMIC ESD, Die Attach and Bonding Guidelines” provides basic information on these subjects.

Additional References:

AN #7, “HMMC-5023 32 GHz Noise Figure Measurements,”
AN #11, “HMMC-5023 as a Doubler to 24 and 28 GHz,” and
AN #13, “HMMC-5023 Configured as a Gain Control Device at 24 and 28 GHz.”

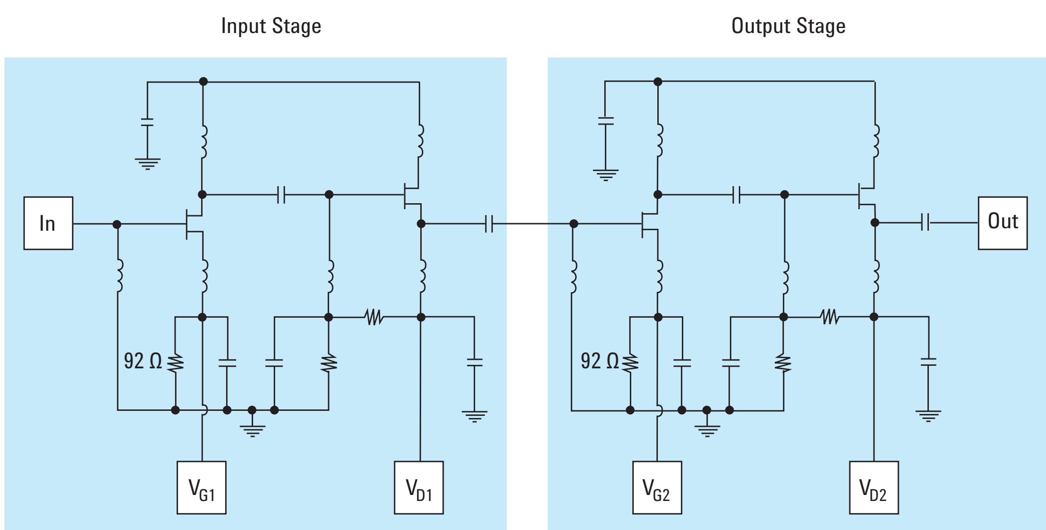


Figure 1. Simplified Schematic Diagram

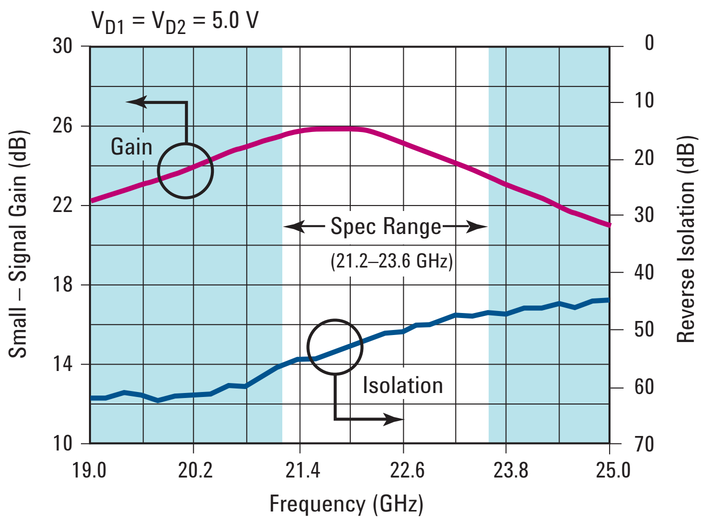


Figure 2. Gain and Isolation vs. Frequency

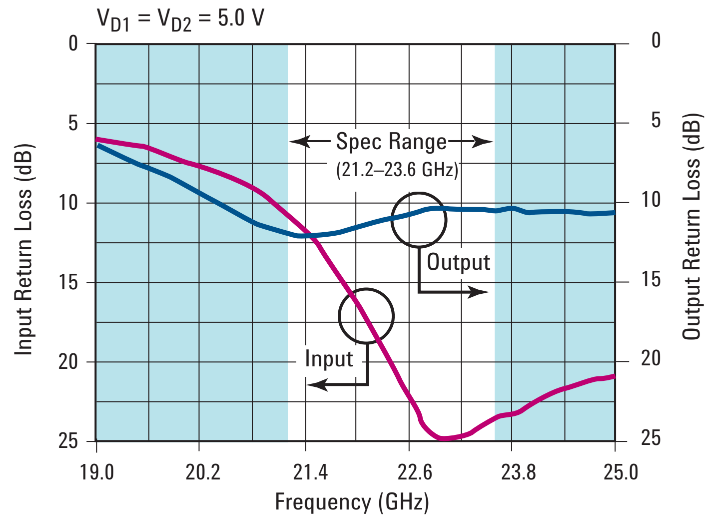


Figure 3. Input and Output Return Loss vs. Frequency

S–Parameters[1]

(T_{op} = 25°C, $V_{D1} = V_{D2} = 5.0$ V, $V_{G1} = V_{G2}$ = Open, Z_o = 50 Ω)

Freq. (GHz)	S_{11}			S_{12}			S_{21}			S_{22}		
	dB	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang
19.0	-6.3	0.486	61.9	-61.6	0.0008	122.7	22.3	13.090	83.3	-6.6	0.470	-179.1
19.2	-6.4	0.477	59.4	-61.6	0.0008	116.3	22.6	13.509	74.2	-6.9	0.450	175.7
19.4	-6.6	0.466	56.7	-61.0	0.0009	113.1	22.5	13.355	64.0	-7.4	0.427	169.7
19.6	-6.8	0.455	53.8	-61.3	0.0009	104.2	23.2	14.459	56.1	-7.9	0.403	163.5
19.8	-7.1	0.443	50.6	-62.3	0.0008	93.0	23.0	14.142	45.0	-8.4	0.381	156.5
20.0	-7.4	0.428	47.1	-61.2	0.0009	72.6	23.5	14.913	36.4	-8.9	0.358	148.8
20.2	-7.8	0.409	43.8	-61.3	0.0009	66.1	23.9	15.599	26.2	-9.5	0.333	139.9
20.4	-8.2	0.391	40.2	-60.9	0.0009	47.3	24.4	16.617	15.7	-10.2	0.309	130.7
20.6	-8.7	0.368	36.2	-59.5	0.0011	25.8	24.7	17.085	5.7	-10.8	0.290	119.5
20.8	-9.3	0.344	31.8	-59.6	0.0011	11.5	25.1	18.061	-4.7	-11.2	0.274	106.2
21.0	-10.0	0.318	27.4	-58.2	0.0012	-4.2	25.4	18.663	-15.3	-11.7	0.259	91.3
21.2	-10.8	0.288	22.9	-56.0	0.0016	-17.6	25.6	19.010	-26.6	-12.0	0.252	74.6
21.4	-11.8	0.256	18.4	-54.9	0.0018	-36.9	25.7	19.209	-38.7	-12.1	0.247	56.4
21.6	-13.1	0.220	14.9	-55.1	0.0018	-52.2	25.7	19.209	-51.3	-12.2	0.247	38.2
21.8	-14.7	0.185	12.1	-53.8	0.0020	-64.6	25.7	19.354	-61.4	-11.9	0.254	21.9
22.0	-16.5	0.149	11.0	-52.5	0.0024	-75.8	25.9	19.769	-74.0	-11.7	0.261	6.8
22.2	-18.5	0.118	12.1	-51.2	0.0028	-90.4	25.6	19.066	-85.2	-11.3	0.271	-6.6
22.4	-20.6	0.094	15.9	-50.5	0.0030	-100.3	25.6	19.113	-96.2	-11.0	0.282	-18.4
22.6	-22.7	0.074	22.8	-50.0	0.0031	-108.7	25.0	17.824	-107.5	-10.7	0.291	-28.7
22.8	-24.3	0.061	37.4	-49.3	0.0034	-118.9	25.1	17.943	-116.9	-10.5	0.298	-37.9
23.0	-24.9	0.057	54.0	-48.5	0.0037	-126.2	24.3	16.401	-127.6	-10.4	0.301	-45.5
23.2	-24.7	0.059	68.3	-47.6	0.0042	-134.9	24.2	16.279	-137.5	-10.4	0.300	-52.3
23.4	-24.2	0.061	78.9	-47.3	0.0043	-144.0	23.9	15.625	-146.3	-10.5	0.298	-58.0
23.6	-23.6	0.066	86.3	-47.2	0.0044	-148.9	23.2	14.469	-154.0	-10.6	0.295	-62.4
23.8	-23.3	0.068	93.5	-46.9	0.0045	-156.1	23.3	14.607	-163.4	-10.5	0.298	-65.9
24.0	-22.6	0.074	98.0	-46.4	0.0048	-161.1	22.4	13.168	-170.8	-10.6	0.296	-69.2
24.2	-22.2	0.078	100.8	-46.1	0.0049	-167.3	22.3	13.002	-179.0	-10.6	0.294	-72.0
24.4	-21.8	0.082	102.8	-45.5	0.0053	-171.7	21.6	12.087	173.1	-10.6	0.294	-74.7
24.6	-21.4	0.086	105.5	-45.6	0.0052	-176.4	21.8	12.350	166.3	-10.7	0.291	-76.8
24.8	-21.2	0.088	108.1	-44.9	0.0057	179.1	21.4	11.771	159.2	-10.8	0.289	-78.4
25.0	-20.9	0.091	293.2	-44.4	0.0061	353.0	21.0	11.257	331.9	-10.8	0.289	-79.3

[1] Data obtained from wafer-probed measurements.

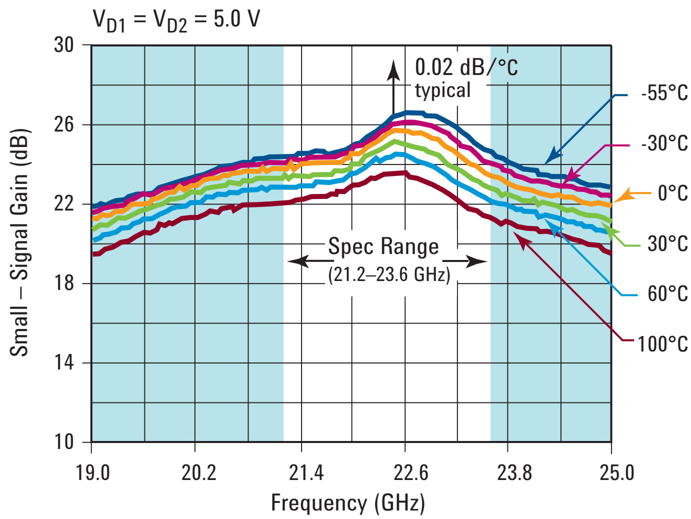


Figure 4. Small-Signal Gain vs. Frequency and Ambient Temperature*

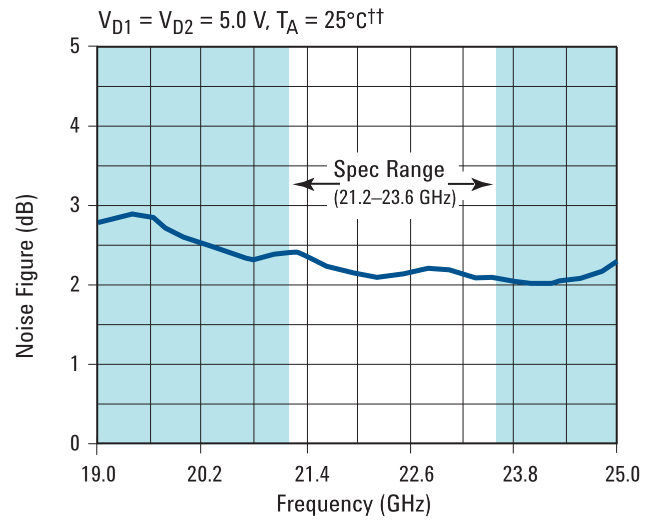


Figure 5. Noise Figure vs. Frequency†

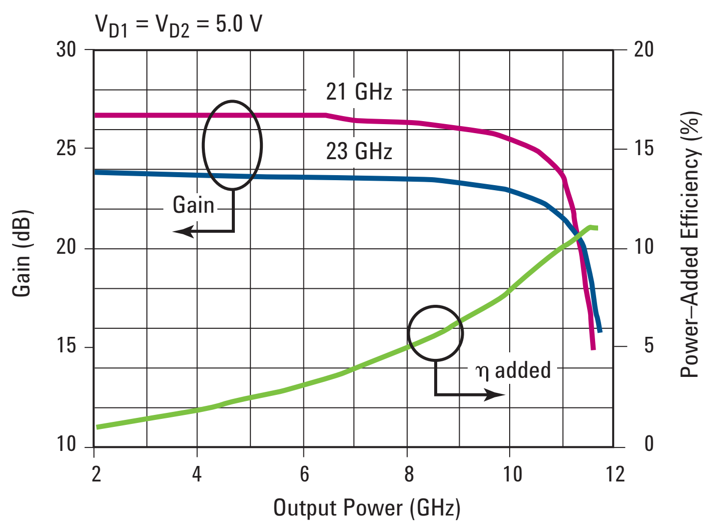


Figure 6. Gain Compression and Efficiency Characteristics†

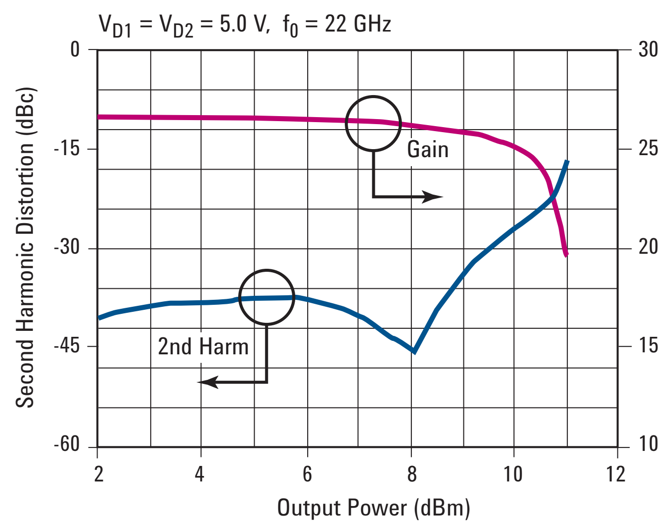


Figure 7. Second Harmonic and Gain Compression Characteristics†

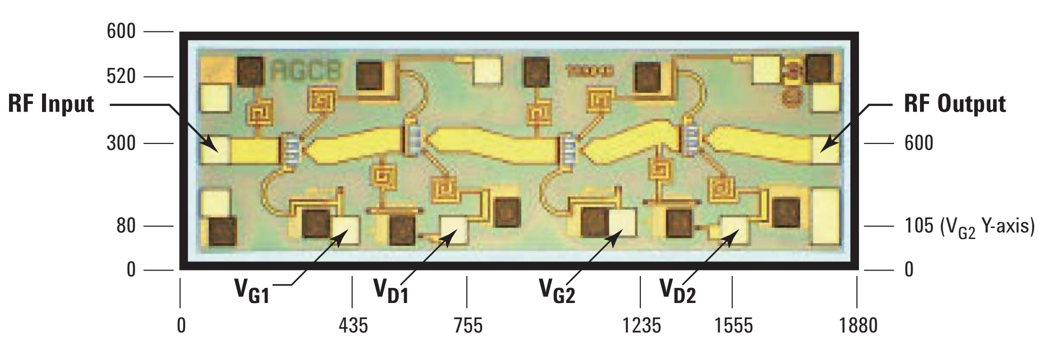
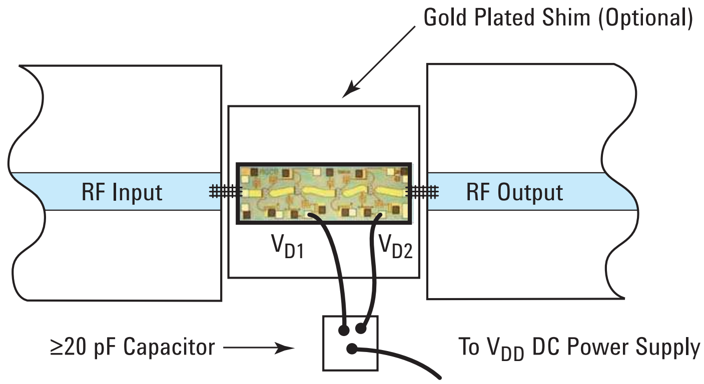


Figure 8. Bonding Pad Positions (Dimensions are micrometers)

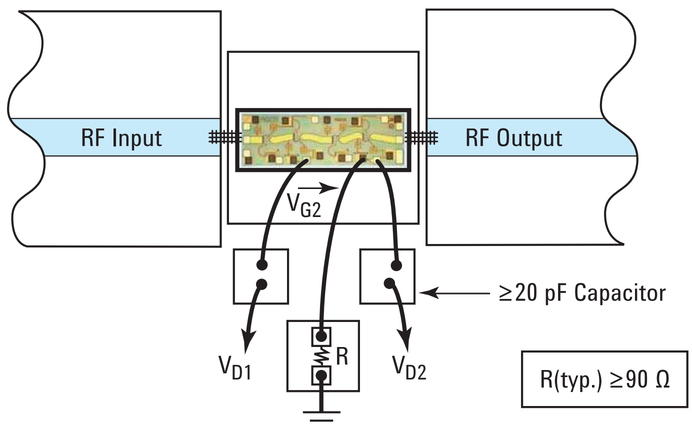
* Device tested while mounted on a Agilent 83040 Modular Microcircuit Fixture calibrated at the coaxial connectors. Test results shown have been degraded by the fixture due to loss and impedance missmatch errors. The temperature coefficient of the fixture alone is approximately 0.003 dB/°C at 20 GHz.

† Data obtained from wafer-probed measurements.

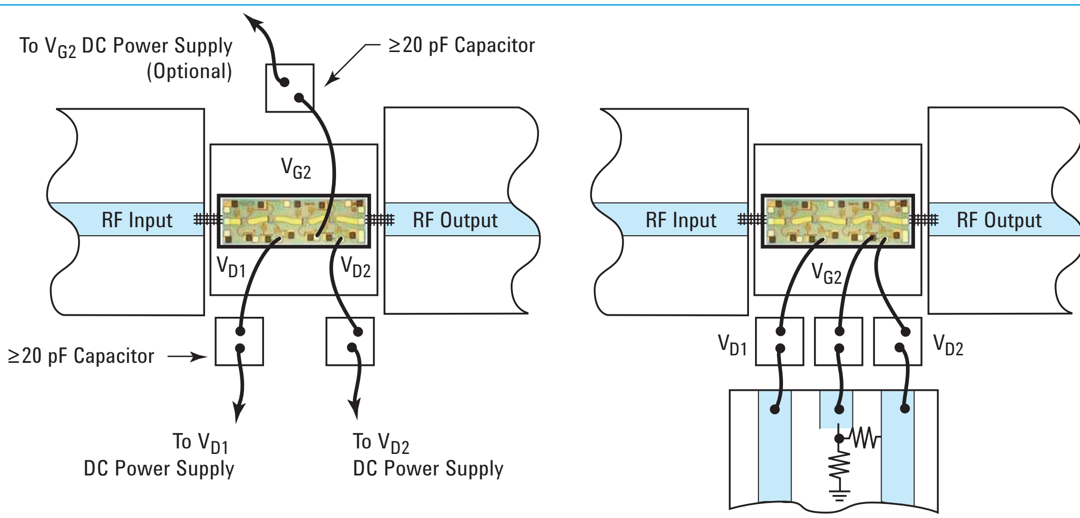
†† The temperature coefficient of noise figure was measured for one device mounted on a Agilent 83040 Modular Microcircuit Fixture. The uncorrected result, <0.014 dB/°C, includes the effects of the fixture.



(a) Single DC Drain Supply.



(b) Assembly for custom biasing of output gain stages using an external chip-resistor.



(c) A VG2 DC supply or a resistive divider network can also be used to bias the output stages for custom applications.

Figure 9. Assembly Diagram Examples

This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. Customers considering the use of this, or other TCA GaAs ICs, for their design should obtain the current production specifications from Agilent TCA Marketing. In this data sheet the term typical refers to the 50th percentile performance. For additional information contact Agilent TCA Marketing at 707-577-4482.

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